



## N-Channel JFETs

**J201**      **SST201**  
**J202**      **SST202**  
**J204**      **SST204**

### PRODUCT SUMMARY

| Part Number | $V_{GS(off)}$ (V) | $V_{(BR)GSS}$ Min (V) | $g_{fs}$ Min (mS) | $I_{DSS}$ Min (mA) |
|-------------|-------------------|-----------------------|-------------------|--------------------|
| J/SST201    | -0.3 to -0.9      | -25                   | 0.5               | 0.7                |
| J/SST202    | -0.8 to -4        | -40                   | 1                 | 0.9                |
| J/SST204    | -0.3 to -2        | -25                   | 0.5               | 0.2                |

### FEATURES

- Low Cutoff Voltage: J201 <1.5 V
- High Input Impedance
- Very Low Noise
- High Gain:  $A_V = 80$  @ 20  $\mu A$

### BENEFITS

- Full Performance from Low Voltage Power Supply: Down to 1.5 V
- Low Signal Loss/System Error
- High System Sensitivity
- High Quality Low-Level Signal Amplification

### APPLICATIONS

- High-Gain, Low-Noise Amplifiers
- Low-Current, Low-Voltage Battery-Powered Amplifiers
- Infrared Detector Amplifiers
- Ultra High Input Impedance Pre-Amplifiers

### DESCRIPTION

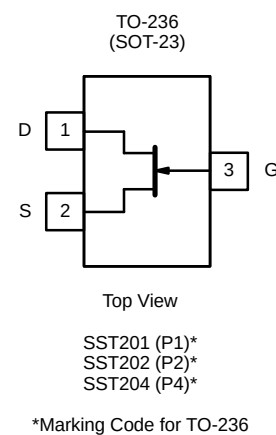
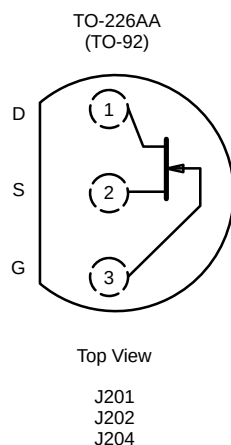
The J/SST201 series features low leakage, very low noise, and low cutoff voltage for use with low-level power supplies. The J/SST201 is excellent for battery powered equipment and low current amplifiers.

The J series, TO-226 (TO-92) plastic package, provides low cost, while the SST series, TO-236 (SOT-23) package, provides surface-mount capability. Both the J and SST series

are available in tape-and-reel for automated assembly (see Packaging Information).

For similar products in TO-206AA (TO-18) packaging, see the 2N4338/4339/4340/4341 data sheet.

For applications information see AN102 and AN106.





## ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage ..... -25 V  
 Gate Current ..... 50 mA  
 Lead Temperature ( $l_{16}$  from case for 10 sec.) ..... 300°C  
 Storage Temperature ..... -55 to 150°C

Operating Junction Temperature ..... -55 to 150°C  
 Power Dissipation<sup>a</sup> ..... 350 mW

## Notes

a. Derate 2.8 mW/°C above 25°C

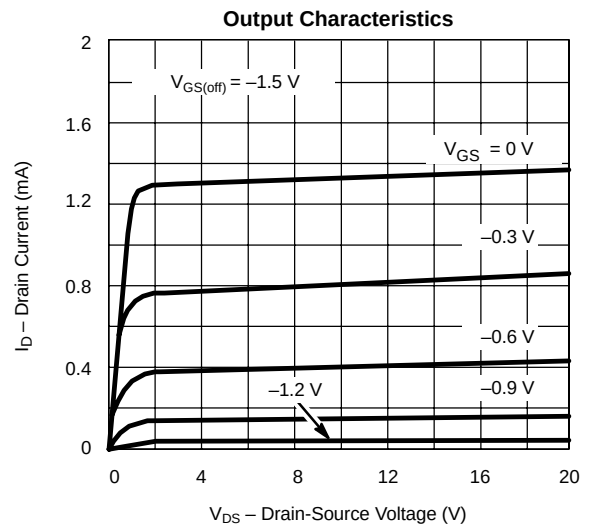
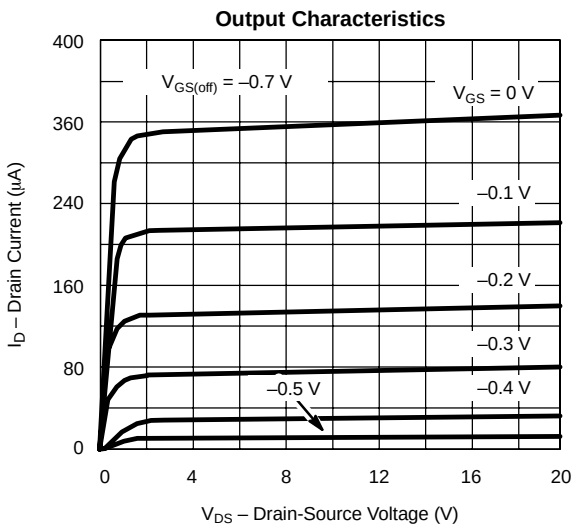
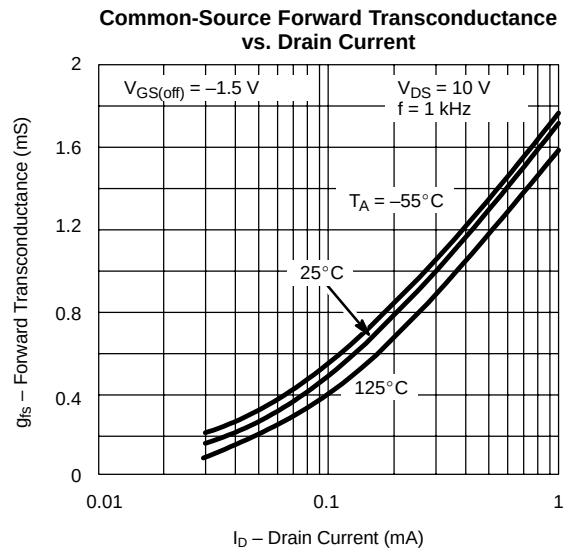
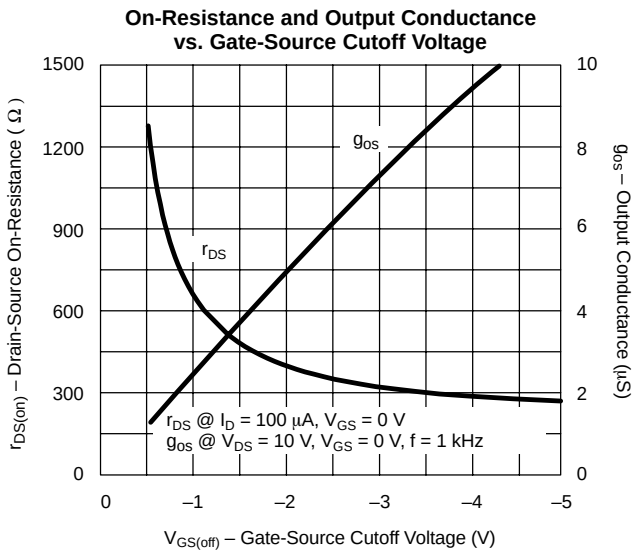
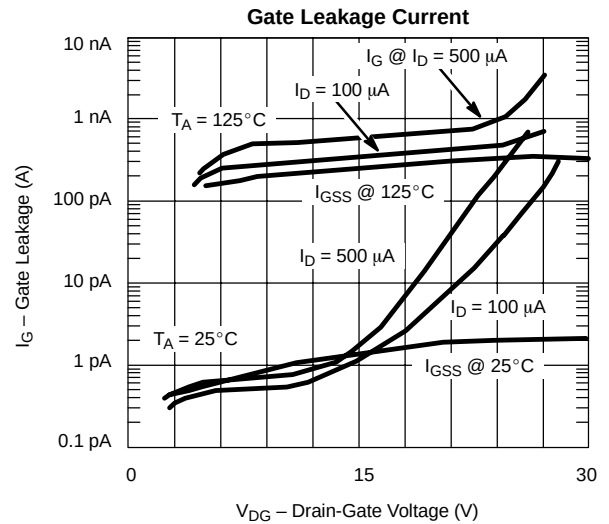
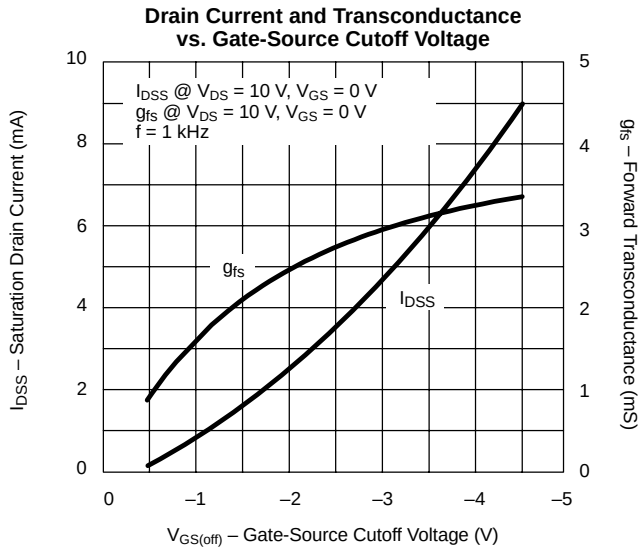
SPECIFICATIONS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)

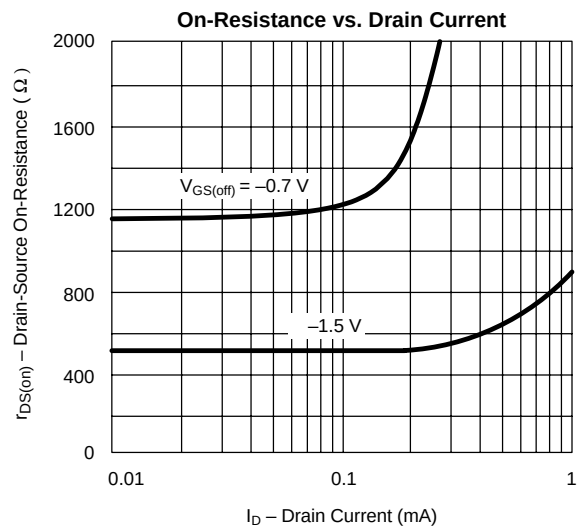
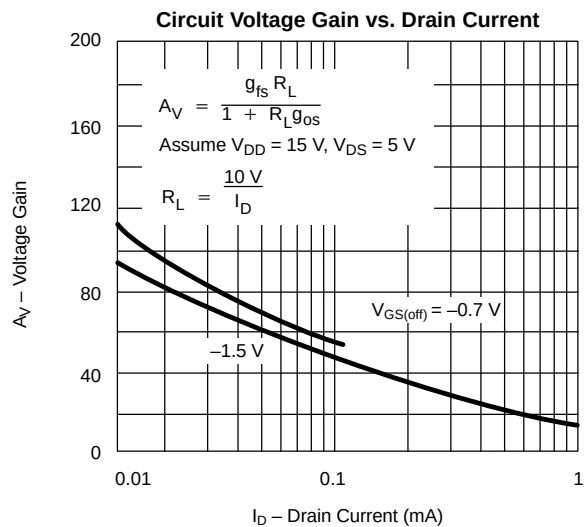
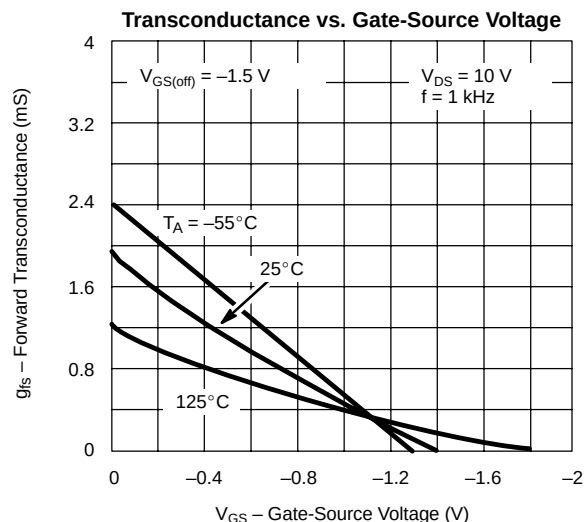
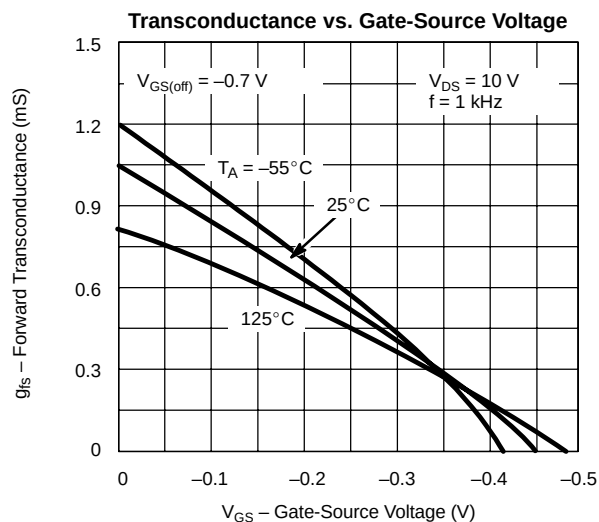
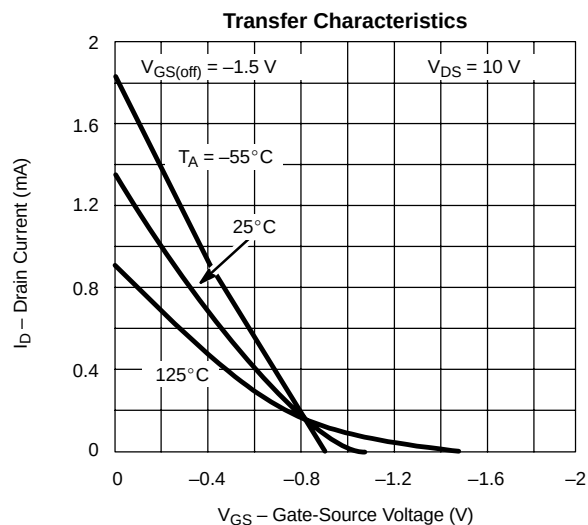
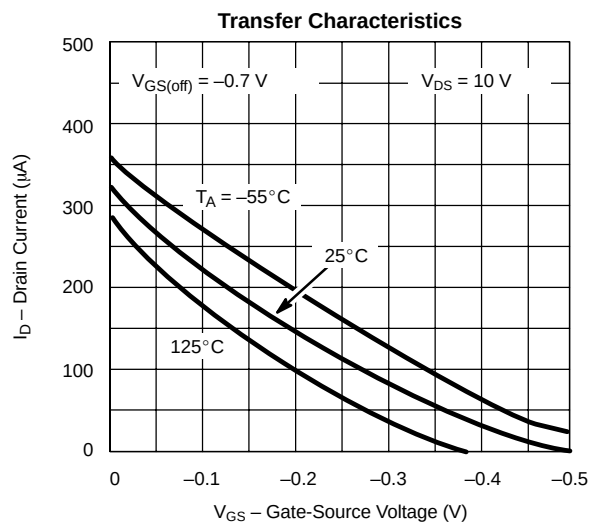
| Parameter                                  | Symbol               | Test Conditions                                            | Typ <sup>a</sup> | Limits   |      |          |      |                       |      | Unit       |
|--------------------------------------------|----------------------|------------------------------------------------------------|------------------|----------|------|----------|------|-----------------------|------|------------|
|                                            |                      |                                                            |                  | J/SST201 |      | J/SST202 |      | J/SST204 <sup>c</sup> |      |            |
|                                            |                      |                                                            |                  | Min      | Max  | Min      | Max  | Min                   | Max  |            |
| Static                                     |                      |                                                            |                  |          |      |          |      |                       |      |            |
| Gate-Source Breakdown Voltage              | V <sub>(BR)GSS</sub> | I <sub>G</sub> = −1 μA , V <sub>DS</sub> = 0 V             |                  | −25      |      | −40      |      | −25                   |      | V          |
| Gate-Source Cutoff Voltage                 | V <sub>GS(off)</sub> | V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 nA             |                  | −0.3     | −0.9 | −0.8     | −4   | −0.3                  | −2   |            |
| Saturation Drain Current <sup>b</sup>      | I <sub>DSS</sub>     | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V              |                  | 0.7      | 1    | 0.9      | 4.5  | 0.7                   | 3    | mA         |
| Gate Reverse Current                       | I <sub>GSS</sub>     | V <sub>GS</sub> = −20 V, V <sub>DS</sub> = 0 V             | −2               |          | −100 |          | −100 |                       | −100 | pA         |
|                                            |                      | T <sub>A</sub> = 125°C                                     | −1               |          |      |          |      |                       |      | nA         |
| Gate Operating Current                     | I <sub>G</sub>       | V <sub>DG</sub> = 10 V, I <sub>D</sub> = 0.1 mA            | −2               |          |      |          |      |                       |      | pA         |
| Drain Cutoff Current                       | I <sub>D(off)</sub>  | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = −5 V             | 2                |          |      |          |      |                       |      |            |
| Gate-Source Forward Voltage                | V <sub>GS(F)</sub>   | I <sub>G</sub> = 1 mA , V <sub>DS</sub> = 0 V              | 0.7              |          |      |          |      |                       |      | V          |
| Dynamic                                    |                      |                                                            |                  |          |      |          |      |                       |      |            |
| Common-Source Forward Transconductance     | g <sub>fs</sub>      | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V<br>f = 1 kHz |                  | 0.5      |      | 1        |      | 0.5                   |      | mS         |
| Common-Source Input Capacitance            | C <sub>iss</sub>     | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V<br>f = 1 MHz | 4.5              |          |      |          |      |                       |      | pF         |
| Common-Source Reverse Transfer Capacitance | C <sub>rss</sub>     |                                                            | 1.3              |          |      |          |      |                       |      |            |
| Equivalent Input Noise Voltage             | $\bar{e}_n$          | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V<br>f = 1 kHz | 6                |          |      |          |      |                       |      | nV/<br>√Hz |

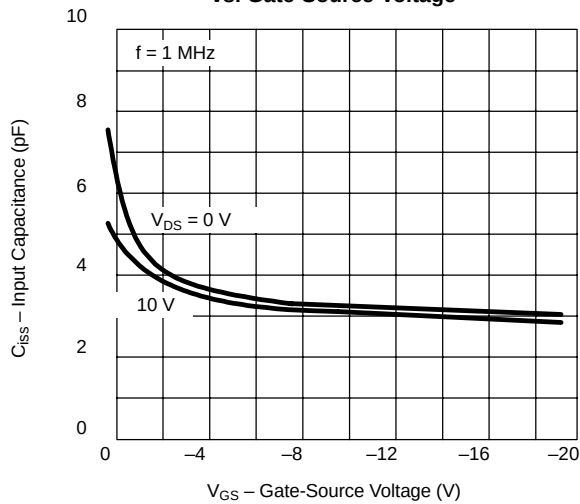
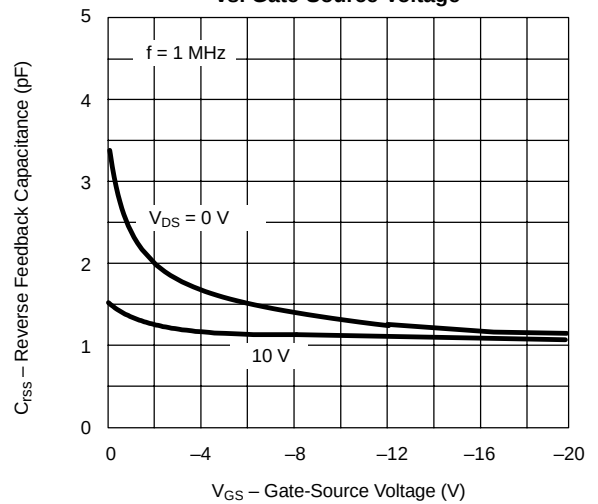
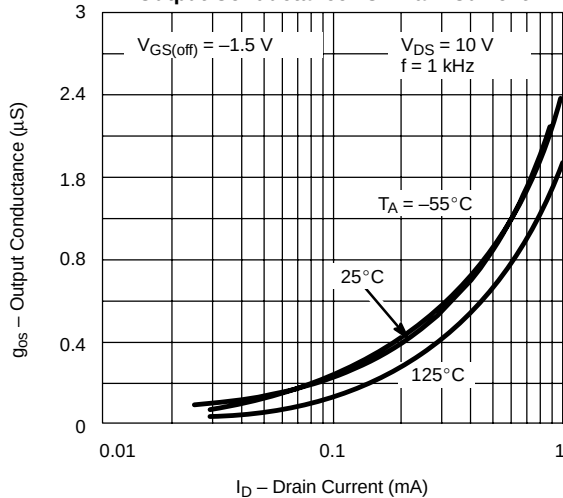
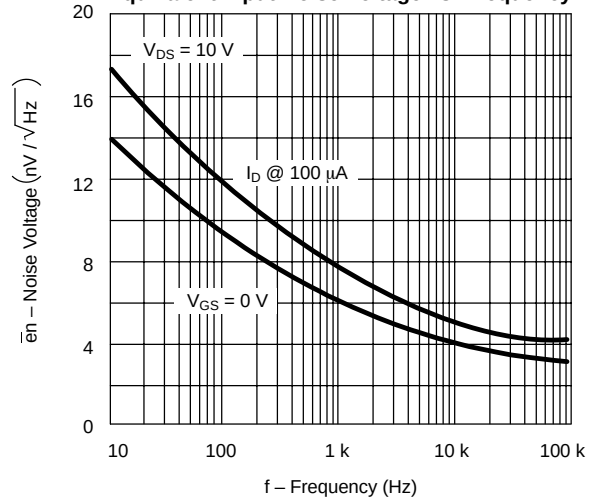
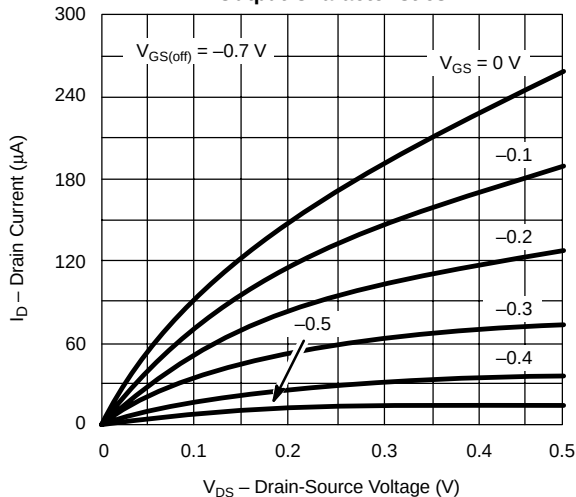
## Notes

- a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.  
 b. Pulse test:  $PW \leq 300\ \mu\text{s}$  duty cycle  $\leq 3\%$ .  
 c. See 2N/SST5484 Series for J204 typical characteristic curves.

NPA, NH

**TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)**

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**TYPICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  UNLESS OTHERWISE NOTED)****Common-Source Input Capacitance vs. Gate-Source Voltage****Common-Source Reverse Feedback Capacitance vs. Gate-Source Voltage****Output Conductance vs. Drain Current****Equivalent Input Noise Voltage vs. Frequency****Output Characteristics****Output Characteristics**